NSN 5961-01-123-8657

Diode Semiconductor Device - Page 1 of 2

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Inclosure Material:

Glass and metal

Overall Length:

Between 0.293 inches and 0.357 inches

Terminal Length:

Between 1.000 inches and 1.625 inches

Overall Diameter:

Between 0.215 inches and 0.235 inches

Function For Which Designed:

Transient suppressor

End Application:

Tacamo tip e/i fscm 13499

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

Do-13

Electrode Internally-electrically Connected To Case:

Cathode

Mounting Method:

Terminal

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

15.8 breakdown voltage, dc

Current Rating Per Characteristic:

1.00 milliamperes forward current, average peak

Power Rating Per Characteristic:

1.0 watts small-signal input power, common-collector major

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius ambient air

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

2 uninsulated wire lead

Specification Data:

81349-mil-s-19500/500 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0